

Application Number 10/655,423  
Amendment dated November 3, 2005  
Reply to Office Action of August 15, 2005

Amendments to the Specification:

Please replace the paragraph at page 5, lines 1-5 with the following amended paragraph:

Referring to FIG. 2, a first etching process is performed using the photoresist layer pattern 108 as an etching mask so that portions of the mask layer 106 and the insulating layer 104 are removed sequentially. After the first etching process, a mask layer pattern 107 is formed, and first to third trenches 121, 122, and 123 having a first thickness or depth  $d_1$  are formed in the insulating layer 104.

Please replace the paragraph at page 5, lines 11-19 with the following amended paragraph:

Referring to FIG. 4, a second etching process is performed using the photoresist layer pattern 130 and the exposed portions of the mask layer pattern 107 as an etching mask, so that a portion of the exposed insulating layer 104 is removed. After the second etching process, a fourth trench 140 having a second thickness depth  $d_2$  thicker deeper than the first thickness depth  $d_1$  is formed in the insulating layer 104. Since the first and third trenches 121 and 123 are covered with the photoresist layer pattern 130 during the second etching process, the first and third trenches 121 and 123 are not affected by the second etching process so that the thicknesses depths of the first and third trenches 121 and 123 are maintained to the first thickness depth  $d_1$ .

Please replace the paragraph at page 5, lines 20-23 with the following amended paragraph:

Referring to FIG. 5, the photoresist layer pattern 130 (refer to FIG. 4) is removed. Thus, the mask layer pattern 107 is exposed, and simultaneously the first and third trenches 121 and 123 of the first thickness depth  $d_1$  and the fourth trench 140 of the second thickness depth  $d_2$  are exposed.